

## D882 TRANSISTOR (NPN)

### FEATURES

Power dissipation

$P_{CM}$ : 500 mW ( $T_{amb}=25^{\circ}C$ )

Collector current

$I_{CM}$ : 3 A

Collector-base voltage

$V_{(BR)CBO}$ : 40 V

Operating and storage junction temperature range

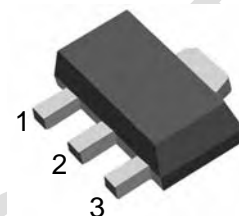
$T_J, T_{stg}$ :  $-55^{\circ}C$  to  $+150^{\circ}C$

### SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10 mA, I_B=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=40 V, I_E=0$			1	$\mu A$
Collector cut-off current	$I_{CEO}$	$V_{CE}=30 V, I_B=0$			10	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=6 V, I_C=0$			1	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=2 V, I_C=1 A$	60		400	
	$h_{FE(2)}$	$V_{CE}=2 V, I_C=100 mA$	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=2 A, I_B=0.2 A$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=2 A, I_B=0.2 A$			1.5	V
Transition frequency	$f_T$	$V_{CE}=5 V, I_C=0.1 A$ $f=10 MHz$	50			MHz

### CLASSIFICATION OF $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400